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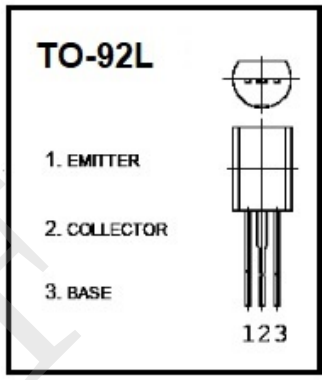
PNP Silicon Transistor

# 2SA928A

- **Complementary to：2SC2328A**
- **Package：TO-92L**

## Maximum Ratings (Ta = 25°)

| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Collector-base voltage | $BV_{CBO}$ | -30 | V |
| Collector-emitter voltage | $BV_{CEO}$ | -30 | V |
| Emitter-base voltage | $BV_{EBO}$ | -5 | V |
| Collector current | $I_{CM}$ | -2 | A |
| Collector Power Dissipation | $P_C$ | 625 | mW |
| Junction Temperature | Tj | 150 | ℃ |
| Storage Temperature | Tstg | -55～+150 | ℃ |




## Electrical Characteristics（Ta=25℃）

| Parameter | Symbol | Test Condition | Min | Max | Unit |
|---|---|---|---|---|---|
| Collector-Base Breakdown Voltage | $BV_{CBO}$ | $I_C$=-100μA，$I_E$=0 | -30 | | V |
| Collector-Emitter Breakdown Voltage | $BV_{CEO}$ | $I_C$=-10mA，$I_B$=0 | -30 | | V |
| Emitter-Base Breakdown Voltage | $BV_{EBO}$ | $I_E$=-1mA，$I_C$=0 | -5 | | V |
| collector-base cut-off current | $I_{CBO}$ | $V_{CB}$=-30V，$I_E$=0 | | -0.1 | μA |
| collector-emitter cut-off current | $I_{CEO}$ | $V_{CE}$=-30V，$I_B$=0 | | -1.0 | μA |
| emitter-base cut-off current | $I_{EBO}$ | $V_{EB}$=-5V，$I_C$=0 | | -0.1 | μA |
| DC current gain | $H_{FE1}$ | $V_{CE}$=-2V，$I_C$=-0.5A | 100 | 320 | |
| collector-emitter saturation voltage | $V_{CESAT}$ | $I_C$=-1.5A，$I_B$=-30mA | | -0.5 | V |
| Base-Emitter Saturation Voltage | $V_{BESAT}$ | $I_C$=-1.5A，$I_B$=-30mA | | -1.2 | |
| Transition frequency | $f_T$ | $V_{CE}$=-5V，$I_C$=-500mA | | 120 | $MH_Z$ |

## Classification of $H_{FE}$

| Rank | 2SA928A-O | 2SA928A-Y |
|---|---|---|
| Range | 100-200 | 160-320 |